8-Bit Dual-Supply Non-**Inverting Level Translator**

The NLSV8T244 is a 8-bit configurable dual-supply voltage level translator. The input A_n and output B_n ports are designed to track two different power supply rails, V_{CCA} and V_{CCB} respectively. Both supply rails are configurable from 0.9 V to 4.5 V allowing universal low-voltage translation from the input A_n to the output B_n port.

Features

- Wide V_{CCA} and V_{CCB} Operating Range: 0.9 V to 4.5 V
- High-Speed w/ Balanced Propagation Delay
- Inputs and Outputs have OVT Protection to 4.5 V
- Non-preferential V_{CCA} and V_{CCB} Sequencing
- Outputs at 3-State until Active V_{CC} is Reached
- Power-Off Protection
- Outputs Switch to 3-State with V_{CCB} at GND
- Ultra-Small Packaging: 4.0 mm x 2.0 mm UDFN20
- This is a Pb-Free Device

Typical Applications

Mobile Phones, PDAs, Other Portable Devices

Important Information

• ESD Protection for All Pins:



ON Semiconductor®

http://onsemi.com

MARKING **DIAGRAMS**



UQFN20 **MU SUFFIX** CASE 517AK



Specific Device Code Date Code

Pb-Free Package



SOIC-20 DW SUFFIX CASE 751D



= Assembly Location = Wafer Lot = Year = Work Week = Pb-Free Package



TSSOP-20 **DT SUFFIX CASE 948E**



= Assembly Location

= Wafer Lot = Year

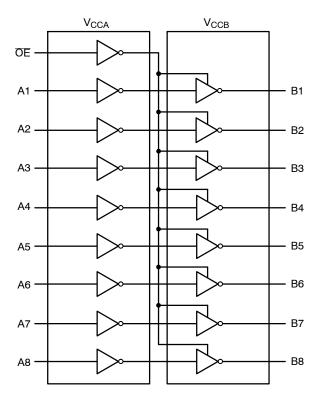
= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.



V_{CCA}	1		V_{CCB}
A1	_2	19	B1
A2	3	18	B2
АЗ	_4		ВЗ
A4			B4
A 5	6		B5
A6	7		B6
A7	8]	13	В7
A8	9	12	B8
GND	10]		ŌĒ
	(Top Vie	W)	

TRUTH TABLE Inputs OE An Bn COE H H X 3-State Figure PIN ASSIGNMENT PIN Voca WCCB GND An Bn OE	OR		B8	× 1 Lasia Biassa	N8
OE An Bn Voca L L L WccB L H H H H X 3-State An Bn OE	ure 2. F	MENDERO	OPA	E	TRUTH TABL
L L L M MCCB GND H X 3-State B _n		PIN	Outputs	nputs	In
L H H GND H X 3-State An B _n		V _{CCA}	Bn	An	ŌĒ
H X 3-State A _n B _n					L
B _n		,	H	H	L
OE OE		A _n	3-State	X	Н
THIS DEV REPREDOCE		B _n	'SK'	- IIIO DI	
THIS D REF.		ŌĒ		E	
				RE	THIS

PIN	FUNCTION
Voca	Input Port DC Power Supply
V _{CCB}	Output Port DC Power Supply
GND	Ground
A _n	Input Port
B _n	Output Port
ŌĒ	Output Enable

MAXIMUM RATINGS

Symbol	Rating		Value	Condition	Unit
V _{CCA} , V _{CCB}	DC Supply Voltage		-0.5 to +5.5		V
V _I	DC Input Voltage	A _n	-0.5 to +5.5		V
V _C	Control Input	ΟE	-0.5 to +5.5		V
Vo	DC Output Voltage (Power Down)	B _n	-0.5 to +5.5	V _{CCA} = V _{CCB} = 0	V
	(Active Mode)	B _n	-0.5 to +5.5		V
	(Tri-State Mode)	B _n	-0.5 to +5.5		V
I _{IK}	DC Input Diode Current		-20	V _I < GND	mA
I _{OK}	DC Output Diode Current		-50	V _O < GND	mA
Io	DC Output Source/Sink Current		±50		mA
I _{CCA} , I _{CCB}	DC Supply Current Per Supply Pin		±100		mA
I _{GND}	DC Ground Current per Ground Pin		±100	(2)	mA
T _{STG}	Storage Temperature		-65 to +150	CIQ!	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CCA} , V _{CCB}	Positive DC Supply Voltage		0.9	4.5	V
VI	Bus Input Voltage	NOV	GND	4.5	V
V_{C}	Control Input	Œ)	GND	4.5	V
V_{IO}	Bus Output Voltage (Po	wer Down Mode) B _n	GND	4.5	V
	C.C.	(Active Mode) B _n	GND	V _{CCB}	V
	R. R.	(Tri-State Mode) B _n	GND	4.5	V
T_A	Operating Temperature Range	THE .	-40	+85	°C
Δt / ΔV	Input Transition Rise or Rate V _I , from 30% to 70% of V _{CC} ; V _{CC} = 3.3 V \pm 0	.3 V	0	10	nS
THIS	S DEVICE PLEESEN				

DC ELECTRICAL CHARACTERISTICS

					−40°C to	+85°C	
Symbol	Parameter	Test Conditions	V _{CCA} (V)	V _{CCB} (V)	Min	Max	Uni
V _{IH}	Input HIGH Voltage		3.6 – 4.5	0.9 – 4.5	2.2	-	V
	(An, \overline{OE})		2.7 – 3.6		2.0	-	
			2.3 – 2.7		1.6	-	
			1.4 – 2.3		0.65 * V _{CCA}	-	
			0.9 – 1.4		0.9 * V _{CCA}	-	
V _{IL}	Input LOW Voltage		3.6 – 4.5	0.9 – 4.5	-	0.8	٧
	(An, \overline{OE})		2.7 – 3.6		_	0.8	
			2.3 – 2.7		_	0.7	
			1.4 – 2.3		_	0.35 * V _{CCA}	
			0.9 – 1.4		_	0.1 * V _{CCA}	
V _{OH}	Output HIGH Voltage	I _{OH} = -100 μA; V _I = V _{IH}	0.9 – 4.5	0.9 – 4.5	V _{CCB} - 0.2	No.	٧
5		$I_{OH} = -0.5 \text{ mA}; V_I = V_{IH}$	0.9	0.9	0.75 * V _{CCB}	CIG	
		$I_{OH} = -2 \text{ mA}; V_I = V_{IH}$	1.4	1.4	1.05	-	
		$I_{OH} = -6 \text{ mA}; V_I = V_{IH}$	1.65	1.65	1\25	_	
		1011 , .	2.3	2.3	2.0	_	
		I _{OH} = -12 mA; V _I = V _{IH}	2.3	2.3	1.8	_	
		10H = 12 110 1, 17 = 17H	2.7	2.7	2.2	<u> </u>	
		$I_{OH} = -18 \text{ mA; } V_{I} = V_{IH}$	2		1.7	_	
		IOH = -10 IIIA, V = V H	2.3	2.3			
			3.0		2.4	-	
W	Output I OW/ Voltage	$I_{OH} = -24 \text{ mA}; V_I = V_{IH}$	3.0	3.0	2.2	-	V
V _{OL}	Output LOW Voltage	$I_{OL} = 100 \mu\text{A}; V_{I} = V_{IL}$	0.9 – 4.5	0.9 – 4.5	-	0.2	٧
		$I_{OL} = 0.5 \text{ mA}; V_I = V_{IL}$	1.0	1.1	-	0.3	
		$I_{OL} = 2 \text{ mA}; V_I = V_{IL}$	(1)4	1.4	-	0.35	
		$I_{OL} = 6 \text{ mA}; V_I = V_{IL}$	1.65	1.65	-	0.3	
	Ch	I_{OL} = 12 mA; V_I = V_{IL}	2.3	2.3	-	0.4	
		5 11 r	2.7	2.7	-	0.4	
	IICE IE	$I_{OL} = 18 \text{ mA}; V_I = V_{IL}$	2.3	2.3	-	0.6	
	ENIPPO		3.0	3.0	-	0.45	
	OF ICE PLEA	I_{OL} = 24 mA; V_I = V_{IL}	3.0	3.0	-	0.6	
h , ;	Input Leakage Current	$V_I = V_{CCA}$ or GND	0.9 - 4.5	0.9 - 4.5	-1.0	1.0	μΑ
l _{OFF}	Power-Off Leakage Current	<u>OE</u> = 0 V	0 0.9 – 4.5	0.9 – 4.5 0	-1.0 -1.0	1.0 1.0	μΑ
I _{CCA}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μ
I _{CCB}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μ
_{CA} + I _{CCB}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	4.0	μ
ΔI_{CCA}	Increase in I _{CC} per Input Voltage, Other Inputs at V _{CCA} or GND	$V_I = V_{CCA} - 0.6 V;$ $V_I = V_{CCA}$ or GND	4.5 3.6	4.5 3.6	-	10 5.0	μ
ΔI_{CCB}	Increase in I _{CC} per Input Voltage, Other Inputs at V _{CCA} or GND	$V_I = V_{CCA} - 0.6 \text{ V};$ $V_I = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	-	10 5.0	μ
l _{OZ}	I/O Tri-State Output Leakage Current	$T_A = 25^{\circ}C, \overline{OE} = 0 \text{ V}$	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μ

TOTAL STATIC POWER CONSUMPTION (I_{CCA} + I_{CCB})

	-40°C to +85°C										
	V _{CCB} (V)										
	4	.5	3	.3	2.	.8	1.	.8	0.	.9	
V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
4.5		2		2		2		2		< 1.5	μΑ
3.3		2		2		2		2		< 1.5	μΑ
2.8		< 2		< 1		< 1		< 0.5		< 0.5	μΑ
1.8		< 1		< 1		< 0.5		< 0.5		< 0.5	μΑ
0.9		< 0.5		< 0.5		< 0.5		< 0.5		< 0.5	μΑ

NOTE: Connect ground before applying supply voltage V_{CCA} or V_{CCB}. This device is designed with the feature that the power–up sequence of V_{CCA} and V_{CCB} will not damage the IC.

AC ELECTRICAL CHARACTERISTICS

							-40°C to	o +85°C				2	
		•	V _{CCB} (V)							•			
			4.	.5	3.	3	2.	.8	1,	.8	1.	2	
Symbol	Parameter	V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} ,	Propagation	4.5		1.6		1.8		2.0		2.1		2.3	nS
t _{PHL} (Note 1)	Delay,	3.3		1.7		1.9		2.1	R	2.3		2.6	
(Note 1)	A _n to B _n	2.8		1.9		2.1		2.3),	2.5	12	2.8	
		1.8		2.1		2.4		2.5	250	2.7)	3.0	
		1.2		2.4		2.7	DA	2.8	Un.	3.0		3.3	
t _{PZH} ,	Output	4.5		2.6		3.8	10	4.0	16,	4.1		4.3	nS
t _{PZL} (Note 1)	Enable,	3.3		3.7	N	3.9	40,	4.1		4.3		4.6	
(Note 1)	OE to B _n	2.5		3.9	7	4.1	R	4.3		4.5		4.8	
		1.8		4.1	17	4.4	0,	4.5		4.7		5.0	
		1.2	O_{j}	4.4), "	4.7		4.8		5.0		5.3	
t _{PHZ} ,	Output	4.5	7	2.6	0//	3.8		4.0		4.1		4.3	nS
t _{PLZ} (Note 1)	Disable,	3.3	: No	3.7	1	3.9		4.1		4.3		4.6	
(Note 1)	OE to B _n	2.5	10	3.9		4.1		4.3		4.5		4.8	
	OF	1.8	RV	4.1		4.4		4.5		4.7		5.0	
	115	1.2		4.4		4.7		4.8		5.0		5.3	
t _{OSHL} ,	Output to	4.5		0.15		0.15		0.15		0.15		0.15	nS
t _{OSLH} (Note 1)	Output Skew,	3.3		0.15		0.15		0.15		0.15		0.15	
(NOTE 1)	Time	2.5		0.15		0.15		0.15		0.15		0.15	
		1.8		0.15		0.15		0.15		0.15		0.15	
		1.2		0.15		0.15		0.15		0.15		0.15	

^{1.} Propagation delays defined per Figure 3.

CAPACITANCE

Symbol	Parameter	Test Conditions	Typ (Note 2)	Unit
C _{IN}	Control Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	3.5	pF
C _{I/O}	I/O Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	5.0	pF
C _{PD}	Power Dissipation Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_{I} = 0 \text{ V or } V_{CCA}, f = 10 \text{ MHz}$	20	pF

Typical values are at T_A = +25°C.
 C_{PD} is defined as the value of the IC's equivalent capacitance from which the operating current can be calculated from: I_{CC(operating)} ≅ C_{PD} x V_{CC} x f_{IN} x N_{SW} where I_{CC} = I_{CCA} + I_{CCB} and N_{SW} = total number of outputs switching.

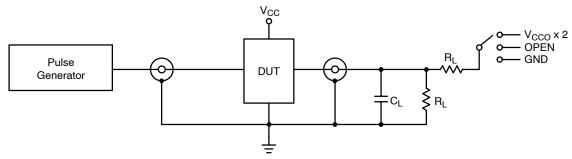


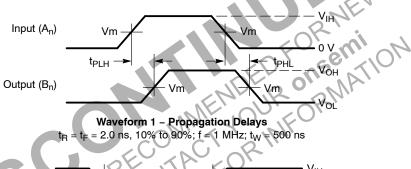
Figure 3. AC (Propagation Delay) Test Circuit

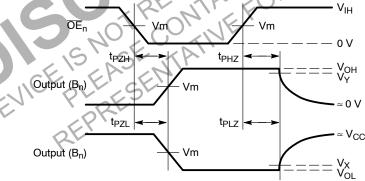
Test	Switch
t _{PLH} , t _{PHL}	OPEN
t_{PLZ} , t_{PZL}	V _{CCO} x 2
t _{PHZ} , t _{PZH}	GND

C_L = 15 pF or equivalent (includes probe and jig capacitance)

 R_L = 2 $k\Omega$ or equivalent

 Z_{OUT} of pulse generator = 50 Ω





Waveform 2 – Output Enable and Disable Times $t_R = t_F = 2.0 \text{ ns}$, 10% to 90%; f = 1 MHz; $t_W = 500 \text{ ns}$

Figure 4. AC (Propagation Delay) Test Circuit Waveforms

		V _{CC}							
Symbol	3.0 V – 4.5 V	2.3 V – 2.7 V	1.65 V – 1.95 V	1.4 V – 1.6 V	0.9 V – 1.3 V				
V _{mA}	V _{CCA} /2								
V _{mB}	V _{CCB} /2								
V _X	V _{OL} x 0.1								
V _Y	V _{OH} x 0.9								

ORDERING INFORMATION

Device	Package	Shipping [†]
NLSV8T244MUTAG	UQFN20 (Pb-Free)	3000 / Tape & Reel
NLSV8T244DTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel
NLSV8T244DWR2G	SOIC-20 (Pb-Free)	1000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

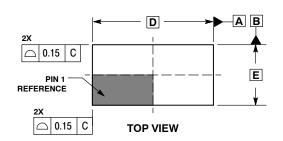






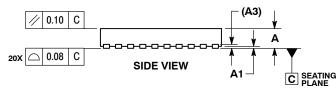
UDFN20 4x2, 0.4P CASE 517AK **ISSUE 0**

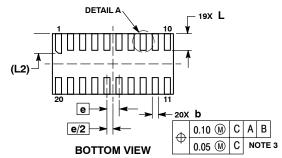
DATE 14 NOV 2006



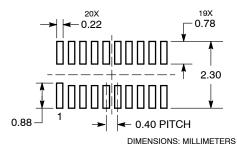


NOTE 5





MOUNTING FOOTPRINT SOLDERMASK DEFINED*



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSIONS 6 APPLIES TO PLATED
 TERMINAL AND IS MEASURED BETWEEN
 0.15 AND 0.30 MM FROM TERMINAL TIP.
- MOLD FLASH ALLOWED ON TERMINALS ALONG EDGE OF PACKAGE. FLASH MAY NOT EXCEED 0.03 ONTO BOTTOM SURFACE OF TERMINALS.
- DETAIL A SHOWS OPTIONAL
 CONSTRUCTION FOR TERMINALS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
A1	0.00	0.05	
A3	0.13 REF		
b	0.15	0.25	
D	4.00 BSC		
Е	2.00 BSC		
е	0.40 BSC		
L	0.50	0.60	
L1	0.00	0.03	
L2	0.60	0.70	

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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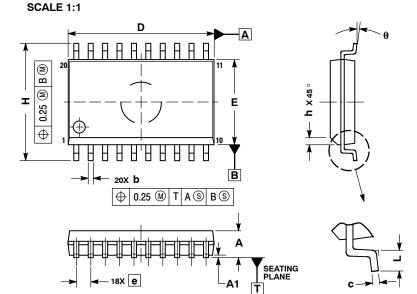
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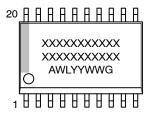
SOIC-20 WB CASE 751D-05 **ISSUE H**

DATE 22 APR 2015



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
b	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
E	7.40	7.60	
е	1.27 BSC		
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
A	0 °	7 °	



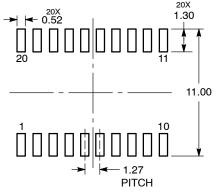
GENERIC MARKING DIAGRAM*

XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

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DESCRIPTION:	SOIC-20 WB		PAGE 1 OF 1

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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